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參考資料目錄:

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A. Papers (期刊論文)

B. Symposium papers (研討會論文)

C. Research project (研究計畫)

D. Patent (專利)

E. International journal reviewer (國際期刊審查委員)

A. Papers(期刊論文)

A1. Y. H. Yeh, C. D. Yang, C. Y. Lee, Y. C. Tseng, and J. D. Tsai "Performance enhancement of InGaN LEDs with Al-graded GaN/AlGaN multiple electron blocking layers", *Jpn. J. Appl. Phys.*, vol. 56, 062102, 2017.

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B. Symposium papers(研討會論文)

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B2. 陳建瑞、鄭仲評、黃紹瑜、蘇水祥、李重義 (2022 年 05 月)。主動層厚度對鈣鈦礦太陽能電池效率之影響。2022 微電子技術發展與應用研討會。

B3. 朱廉軒、郭鐘亮、李重義 (2021 年 05 月)。過驅動下的 UV 及 IR 發光二極體之可靠度測試與故障分析。2021 微電子技術發展與應用研討會。

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B5. 鄭仲評、李昀修、洪嘉徽、李重義 (2021 年 05 月)。溫度和光變化對砷化鎵、矽及氧化銦錫薄膜導電率影響之研究。2021 微電子技術發展與應用研討。

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C. Research project (研究計畫)

C1. “高靜電放電破壞耐受力之氮化鎵系發光二極體之研製”,
106AB002, 主持人, 2017/11~2018/7

C2. “改善高亮度磷化鋁鎵銦發光二極體低溫壽命特性之研究”,
ISU99-01-03, 主持人, 2010/01~2010/12

C3. “新型雙平面摻雜披覆層磷化鋁鎵銦發光二極體之研究”,
ISU98-01-08, 主持人, 2009/01~2009/12

C4. “抗低溫發光二極體之研究與開發”,
ISU97-01-06, 主持人, 2008/01~2008/12

C5. “平面摻雜披覆層多量子井磷化鋁鎵銦發光二極體之研究”,
ISU96-01-05, 主持人, 2007/01~2007/12

C6. “多量子井磷化鋁鎵銦發光二極體接面溫度受工作電流影響之研究”,
ISU95-01-06, 主持人, 2006/01~2006/12

C7. “以 MOCVD 成長並研製調制摻雜磷化鋁銦鎵發光二極體”,
NSC 93-2215-E-214-006, 主持人, 2004/08~2005/07

C8. “以 MOCVD 成長並研製增強型 InGaAs 假晶高速電子遷移率電晶體”,
NSC 92-2215-E-214-005, 主持人, 2003/08~2004/07

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D. Patent (專利)

D1. 李重義、蘇住裕，“調制摻雜多量子井發光二極體”，(中華民國新型第 M 299925 號)，
2006/10/21~2016/5/17

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E. International journal reviewer (國際期刊委員)

E1. IEEE Photonics Technology Letters，2010/3
E2. IEEE Photonics Technology Letters，2009/8
E3. Superlattices and Microstructures，2009/4
E4. IEEE Photonics Technology Letters，2009/2
E5. Physica B，2008/8
E6. IEEE Photonics Technology Letters，2007/10